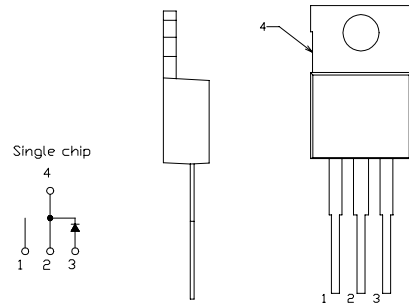


SBD Type : GSH10A10B

OUTLINE DRAWING

FEATURES

- *Similar to TO-220AB Case
- *Low Forward Voltage Drop
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *Tj=150 °C operation



Maximum Ratings

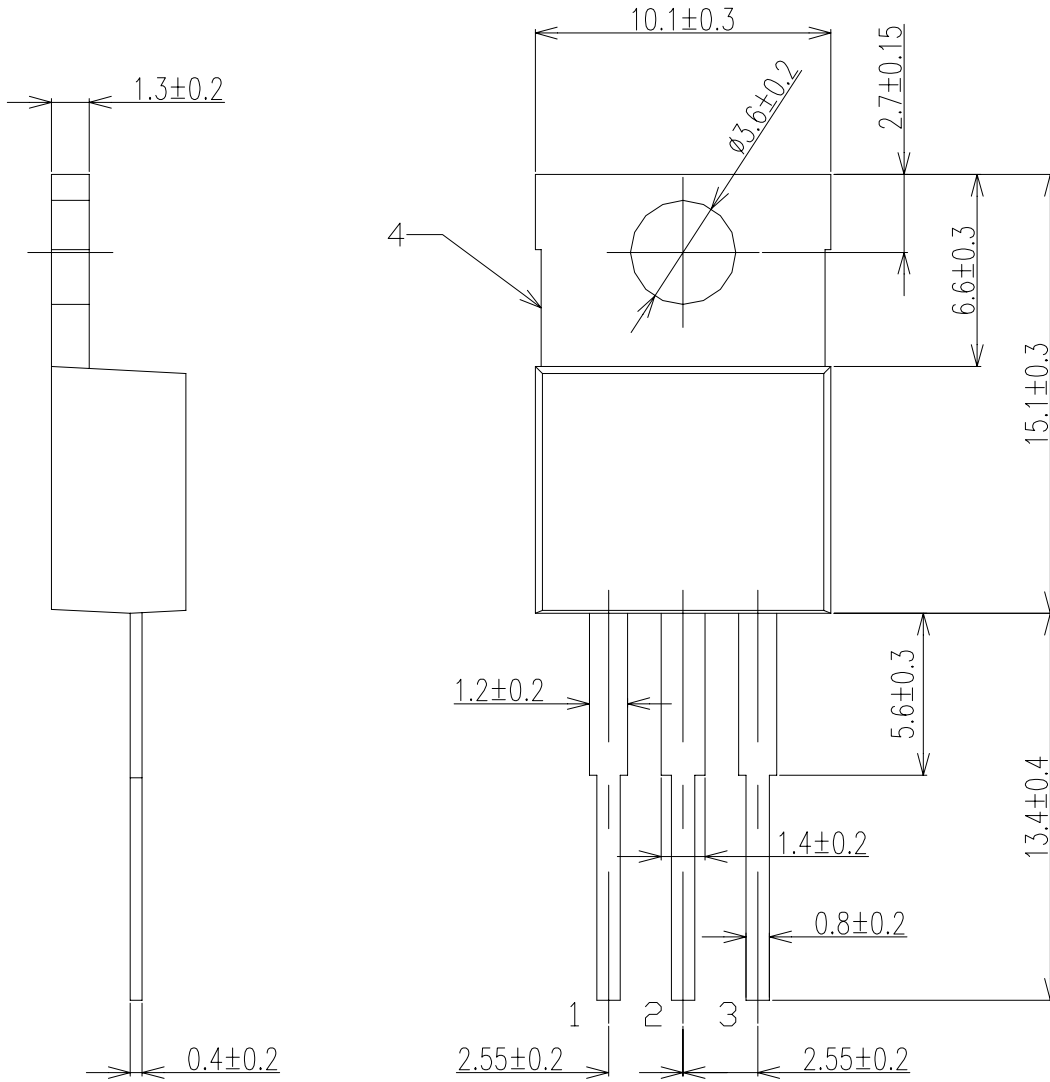
Approx Net Weight: 1.9g

Rating	Symbol	GSH10A10B		Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100		V
Average Rectified Output Current	I_O	10	Tc=120°C 50 Hz half Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	15.7		A
Surge Forward Current	I_{FSM}	180	50Hz Half Sine Wave ,1cycle Non-repetitive	A
Operating JunctionTemperature Range	T_{jw}	-40 to +150		°C
Storage Temperature Range	T_{stg}	-40 to +150		°C
Mounting torque	F_{tor}	recommended torque = 0.5		N•m

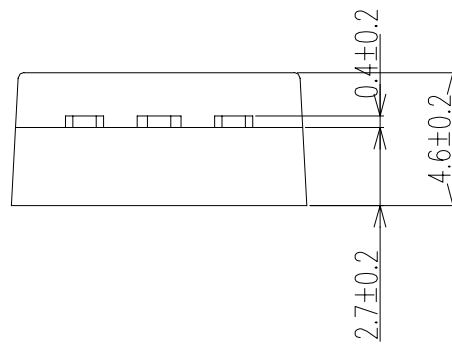
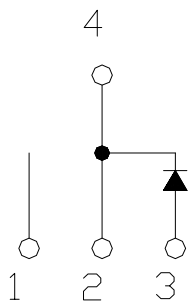
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	Tj= 25°C, $V_{RM}= V_{RRM}$	-	-	1	mA
Peak Forward Voltage	V_{FM}	Tj= 25°C, $I_{FM}= 10 A$	-	-	0.88	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	3	°C /W

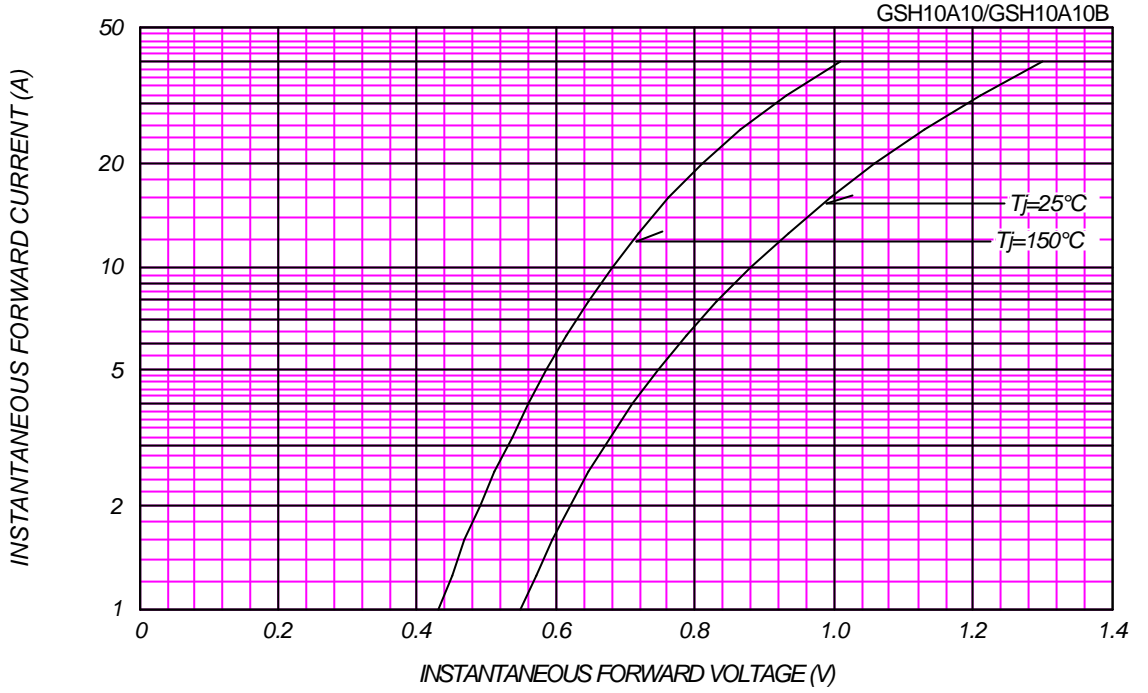
GSH_B_ OUTLINE DRAWING (Dimensions in mm)



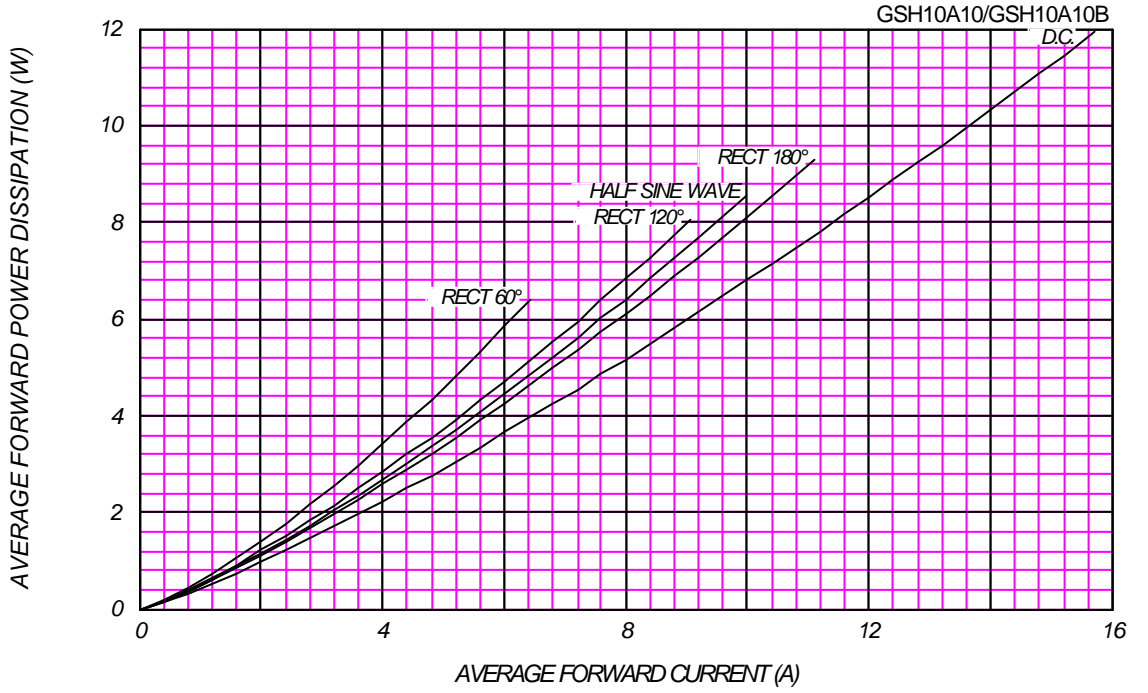
Single chip



FORWARD CURRENT VS. VOLTAGE



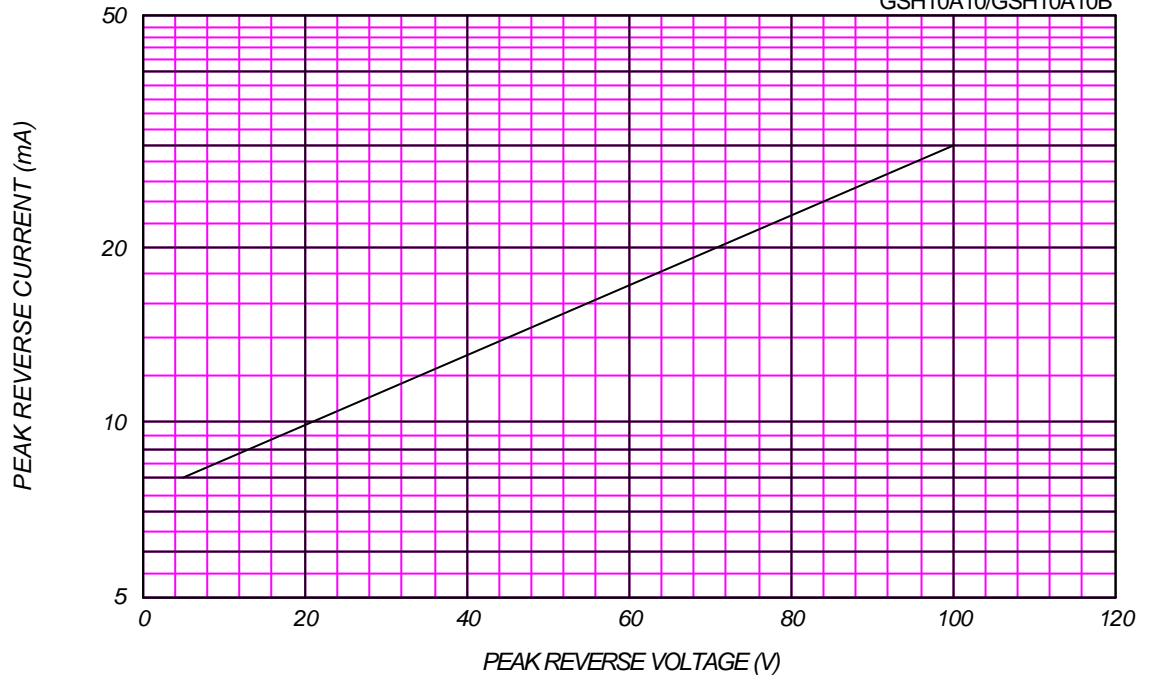
AVERAGE FORWARD POWER DISSIPATION



PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

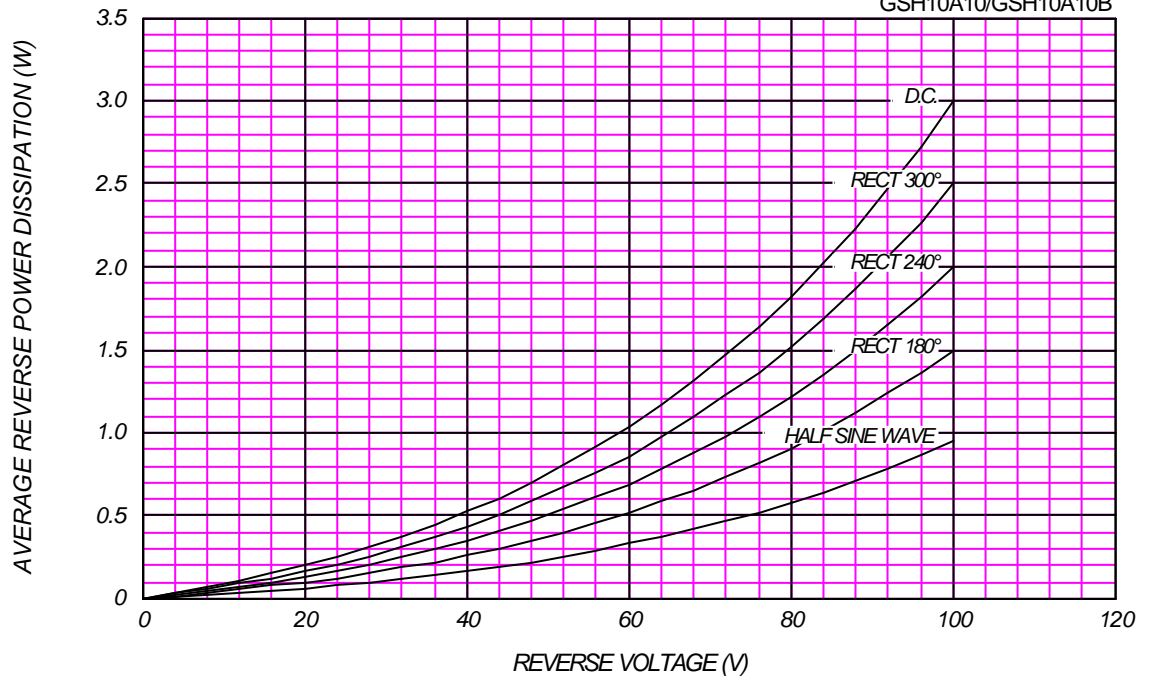
$T_j = 150\text{ }^\circ\text{C}$

GSH10A10/GSH10A10B



AVERAGE REVERSE POWER DISSIPATION

GSH10A10/GSH10A10B

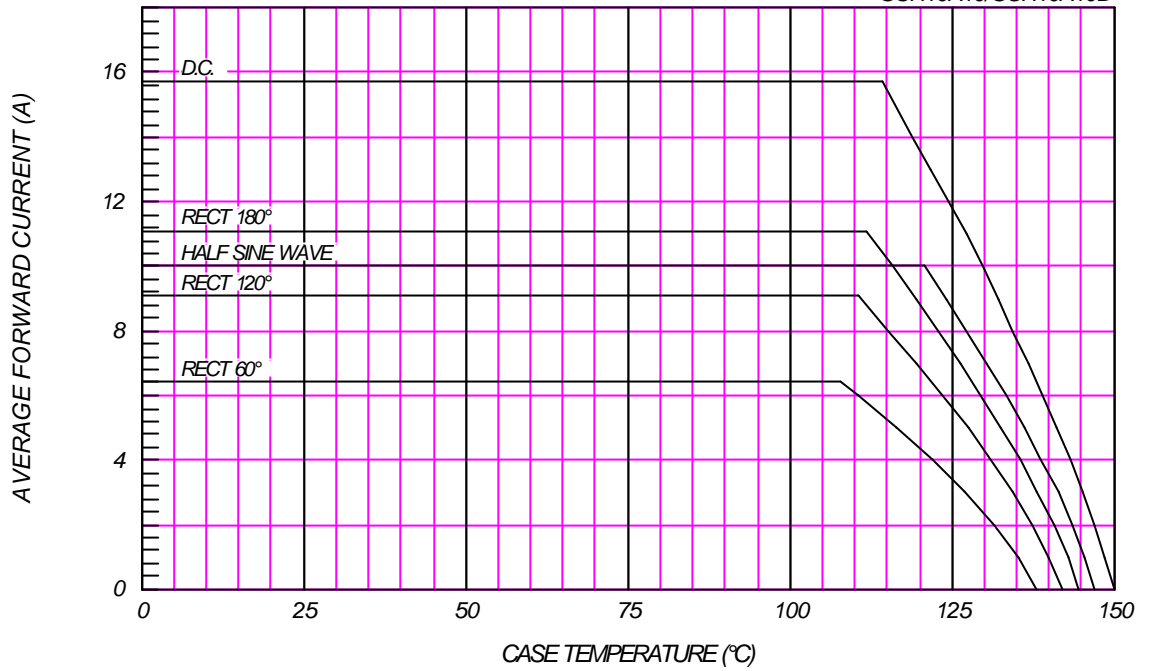




AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

$V_{RM} = 100V$

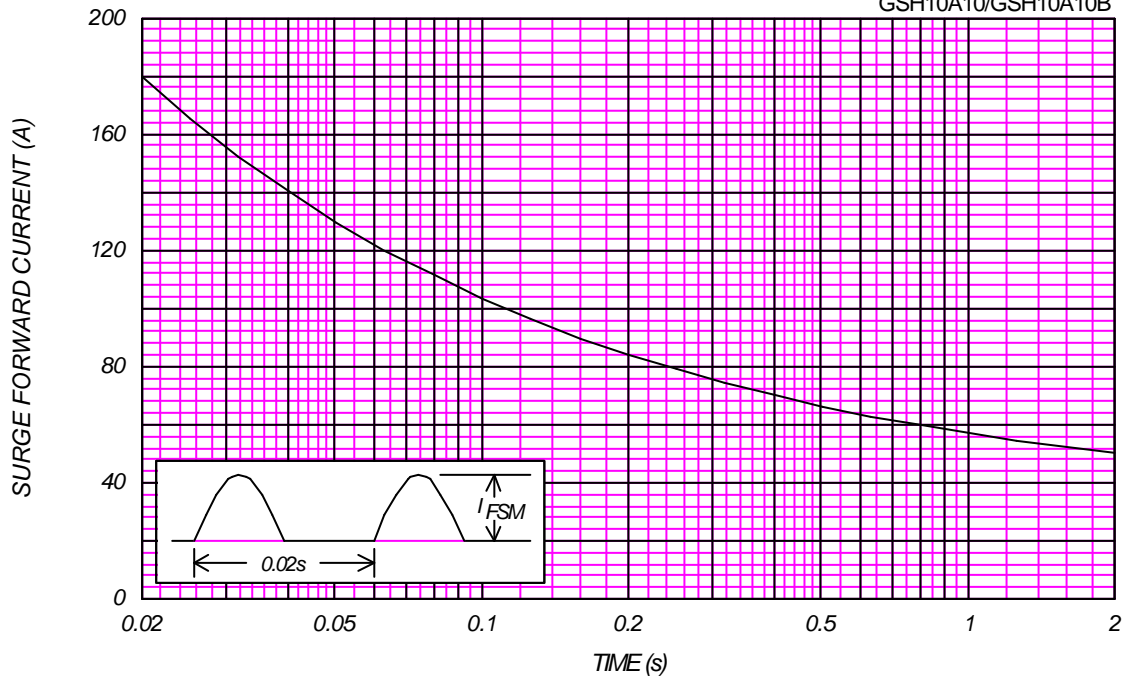
GSH10A10/GSH10A10B



SURGE CURRENT RATINGS

$f = 50Hz$, Half Sine Wave, Non-Repetitive, No Load

GSH10A10/GSH10A10B



JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^\circ\text{C}$, $V_m=20\text{mV}_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

GSH10A10/GSH10A10B

